

# **BUK7Y18-75B**

# N-channel TrenchMOS standard level FET

1 March 2013

**Product data sheet** 

## 1. General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using Nexperia High-Performance Automotive (HPA) TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

#### 2. Features and benefits

- Q101 compliant
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

## 3. Applications

- 12 V, 24 V and 42 V loads
- Automotive systems
- DC-to-DC converters
- Engine management
- General purpose power switching
- Motors, lamps and solenoids
- Transmission control

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	75	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u> ; <u>Fig. 4</u>		-	-	49	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	105	W
Static characteristics							,
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ °C};$ Fig. 12; Fig. 13		-	13.8	18	mΩ
Dynamic characteristics							
$Q_{GD}$	gate-drain charge	I <sub>D</sub> = 20 A; V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 10 V; Fig. 14		-	14.24	-	nC



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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Avalanche rug	Avalanche ruggedness						
E <sub>DS(AL)</sub> S	non-repetitive drain- source avalanche energy	$I_D$ = 49 A; $V_{sup} \le 75$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	118	mJ

## **Pinning information**

Table 2. **Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source	<u> </u>	
3	S	source	q j	G T A
4	G	gate	فققف	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

## **Ordering information**

Table 3. Ordering information

Table 5. Ordering in	ioiiiatioii						
Type number	Package	kage					
	Name	Description	Version				
BUK7Y18-75B	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669				

## **Marking**

Table 4. **Marking codes** 

Type number	Marking code
BUK7Y18-75B	71875B

## **Limiting values**

#### Table 5. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	75	V
$V_{DGR}$	drain-gate voltage	$R_{GS}$ = 20 k $\Omega$	-	75	V
$V_{GS}$	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u> ; <u>Fig. 4</u>	-	49	Α
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Symbol	Parameter	Conditions		Min	Max	Unit
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>		-	34.9	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \mu s$ ; Fig. 4		-	198	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	105	W
T <sub>stg</sub>	storage temperature			-55	175	°C
T <sub>j</sub>	junction temperature			-55	175	°C
Source-drai	in diode			'	'	
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	49	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	198	Α
Avalanche r	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 49 A; $V_{sup}$ ≤ 75 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	118	mJ
E <sub>DS(AL)R</sub>	repetitive drain-source avalanche energy	Fig. 3	[1][2][3]	-	-	J

- [1] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [2] Repetitive avalanche rating limited by an average junction temperature of 170 °C.
- [3] Refer to application note AN10273 for further information.

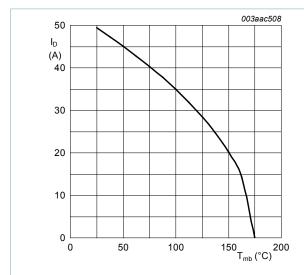


Fig. 1. Continuous drain current as a function of mounting base temperature

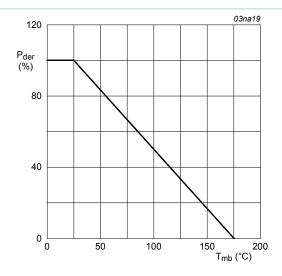
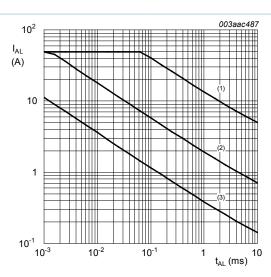


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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- (1) Single pulse;  $T_j = 25$ °C.
- (2) Single pulse;  $T_i = 150$ °C.
- (3) Repetitive.

Fig. 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time

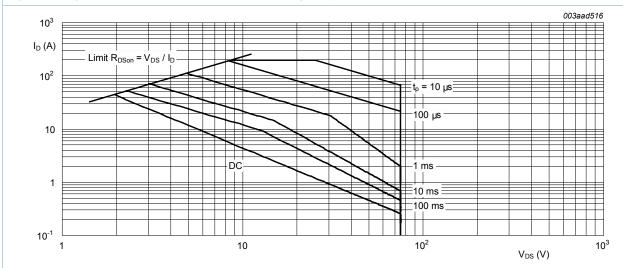


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.

$$T_{mb} = 25 \,^{\circ}C; I_{DM}$$
 is single pulse

#### 9. Thermal characteristics

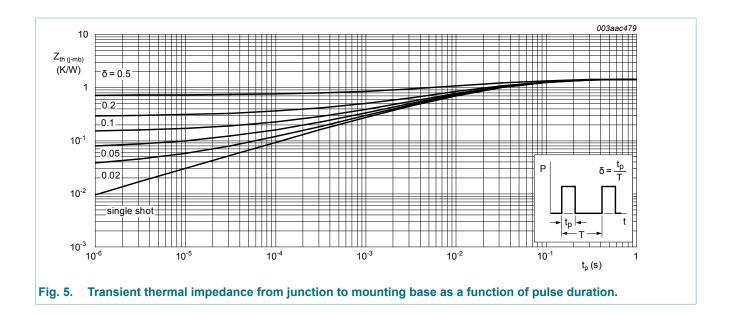
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	-	1.42	K/W

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### 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics			'		
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 ^{\circ}C$	75	-	-	V
	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	68	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; Fig. 10; Fig. 11	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	4.4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10	1	-	-	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 75 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.02	1	μΑ
		V <sub>DS</sub> = 75 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
$R_{DSon}$	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 20 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 13	-	-	43.2	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 20 A; T <sub>j</sub> = 25 °C; Fig. 12; Fig. 13	-	13.8	18	mΩ
Dynamic ch	naracteristics					
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 20 A; V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 10 V;	-	35	-	nC
$Q_{GS}$	gate-source charge	Fig. 14	-	8.28	-	nC
$Q_GD$	gate-drain charge		-	14.24	-	nC

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;		-	1630	2173	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>		-	274	329	pF
C <sub>rss</sub>	reverse transfer capacitance			-	115	158	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 30 V; $R_{L}$ = 1.5 $\Omega$ ; $V_{GS}$ = 10 V; $R_{G(ext)}$ = 10 $\Omega$		-	18.5	-	ns
t <sub>r</sub>	rise time			-	22.5	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	44.5	-	ns
t <sub>f</sub>	fall time			-	19.8	-	ns
Source-dra	ain diode		1			'	,
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 25 V; T <sub>j</sub> = 25 °C; Fig. 16		-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S$ = 20 A; $dI_S/dt$ = -100 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 30 V		-	55.4	-	ns
Q <sub>r</sub>	recovered charge			-	143	-	nC

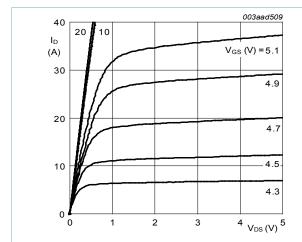


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values.

 $T_j = 25$ °C

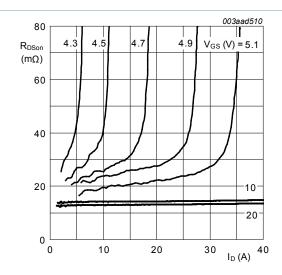


Fig. 7. Drain-source on-state resistance as a function of drain current; typical values.

$$T_j = 25 \,^{\circ}C$$

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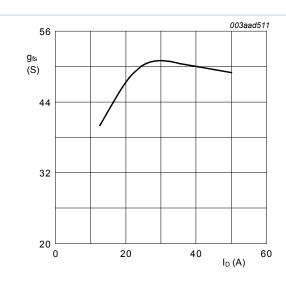


Fig. 8. Forward transconductance as a function of drain current; typical values.

$$T_j = 25 \,^{\circ}C; V_{DS} = 25 \, V$$

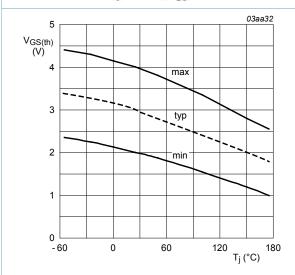


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 mA; V_{DS} = V_{GS}$$

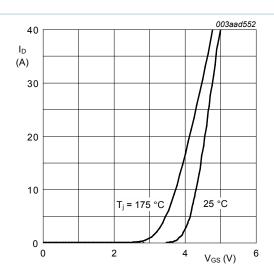


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values.

$$V_{DS}=25\,V$$

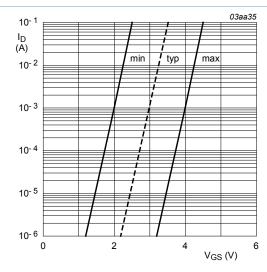


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25$$
 °C;  $V_{DS} = 5V$ 

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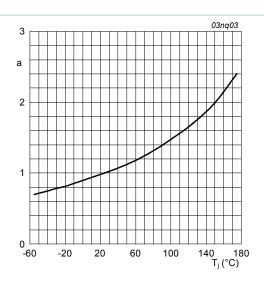


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

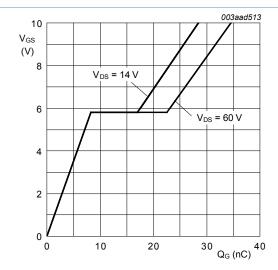


Fig. 14. Gate-source voltage as a function of gate charge; typical values.

$$T_j=25\,^{\circ}C; I_D=20A$$

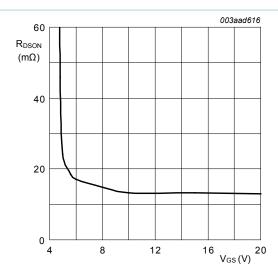


Fig. 13. Drain-source on-state resistance as a function of gate-source voltage; typical values.

$$T_j=25\,^{\circ}C; I_D=20A$$

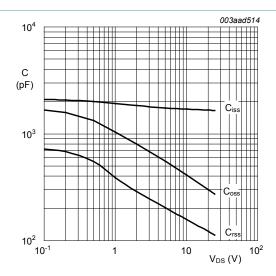


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.

$$V_{GS} = 0V; f = 1MHz$$

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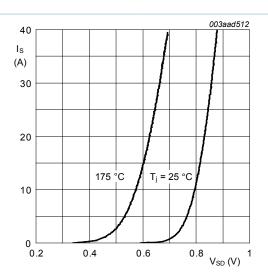


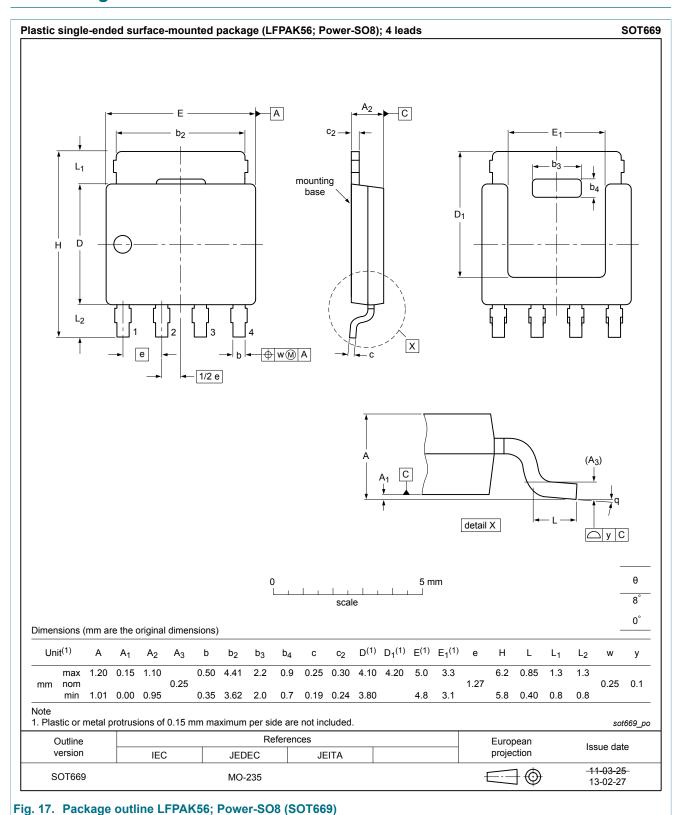
Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values.

$$V_{\rm GS} = 0 \, V$$

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## 11. Package outline



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### 12. Legal information

#### 12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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